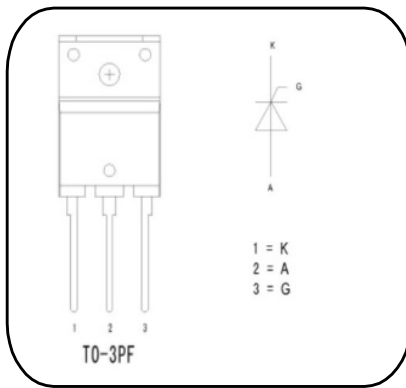


**Typical Applications**

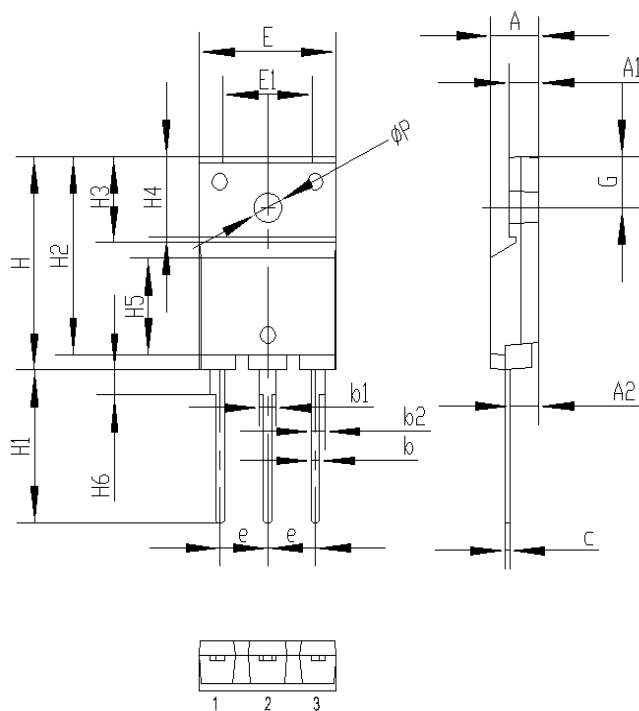
High power industrial and power
transmission
DC and AC motor control
AC controllers

Features

Thyristor for line frequency
Planar passivated chip
Long-term stability

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(RMS)}$	RMS on-state current	180 half sine wave 50Hz	125			80	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM} & V_{RRM} , $t_p=10ms$	125			1600	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			10	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			500	A
I^2t	I^2t for fusing coordination					1250	A ² s
V_{TM}	Peak on-state voltage	$I_{TM}=160A$, $t_p=380\mu s$	25			2.10	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/ μs
di/dt	Critical rate of rise of on-state current		125			150	A/ μs
I_L	Latching current	$I_G=1.2 I_{GT}$	25			250	mA
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$	25	20		70	mA
V_{GT}	Gate trigger voltage					1.5	V
I_H	Holding current					200	mA
V_{GD}	Non-trigger gate voltage	$V_D=12V$	125	0.25			V
$R_{th(j-c)}$	Thermal resistance Junction to case					0.25	°C/W
T_j	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		150	°C
Outline	TO-3PF						

Outline:



Symbol	Dimensions(millimeters)	
	Min.	Max.
A	5.30	5.70
A1	3.25	3.65
A2	3.15	3.55
b	0.80	1.20
b1	1.85	2.15
b2	1.45	1.75
c	0.40	0.80
e	5.25	5.65
E	15.4	15.8
E1	10.0	10.4
H	22.5	23.2
H1	16.0	17.0
H2	21.2	21.6
H3	9.10	9.50
H4	8.55	8.95
H5	10.20	10.60
H6	2.55	2.85
G	5.30	5.70
ϕP	3.00	3.40